Process		NR9 1500PY
Dehydration Bake (hot plate)	temp (˚C)	150
	time (min)	5
Spin coating NR9-1500PY	Speed/acc (rpm)	300
	time (s)	3
	speed (rpm)	3000
	acceleration (rpm/s)	5000
	time (s)	45
Soft-bake (hotplate)	temp (˚C)	150
	time (s)	60
Expose ($12mW/cm^2$)	mode	HC
	time (s)	11
Post Exposure Bake (hot plate)	temp (˚C)	100
	time (min)	60
Develop	developer	RD 6
	developer: di water ratio	3:1
	time (sec) (approx.)	25-30
Rinse in DI water	time (min)	2

NB:

1. SC: Soft Contact; HC: Hard Contact; VC: Vacuum Contact; LVC: Low Vacuum Contact
2. Development of NR9-1500PY is accomplished in a basic water solution (RD6)
3. If exposure is insufficient, bleaching within the exposed areas will be observed after development. This should not happen with sufficiently exposed resist surface which should be fully cross-linked.
4. NR9-1500PY can be removed using acetone, 1165 remover, RR5 or RR4 strippers.
5. These are results using a bare Silicon substrate. Films on substrates and/or use of other types of substrates may affect the exposure and/or development time. Adjust as needed.
6. Use of this process data should act as a guide to developing and/or refining your process rather than being adopted as is. The process was used to resolve a minimum feature size of 2 µm.